

OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

MPPS™ Miniature Package Power Solutions COMPLEMENTARY DUAL 20V LOW SATURATION TRANSISTOR

SUMMARY

NPN Transistor — $V_{CE0} = 20V$; $R_{SAT} = 47m\Omega$; $I_C = 4.5A$

PNP Transistor — $V_{CE0} = -20V$; $R_{SAT} = 64m\Omega$; $I_C = -3.5A$

DESCRIPTION

Packaged in the new innovative 3mm x 2mm MLP (Micro Leaded Package), these low saturation NPN / PNP combination dual transistors offer lower on state losses making them ideal for use in DC-DC circuits and various driving and power-management functions.

Users will also gain several other **key benefits**:

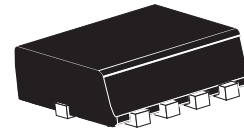
Performance capability equivalent to much larger packages

Improved circuit efficiency & power levels

PCB area and device placement savings

Lower package height (0.9mm nom)

Reduced component count



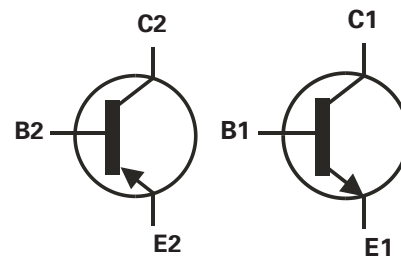
3mm x 2mm Dual Die MLP

FEATURES

- Low Equivalent On Resistance
- Low Saturation Voltage (**150mV max @1A--NPN**)
- H_{FE} specified up to 6A
- $I_C = 4.5A$ Continuous Collector Current
- 3mm x 2mm MLP

APPLICATIONS

- DC - DC Converters
- Charging circuits
- Power switches
- Motor control



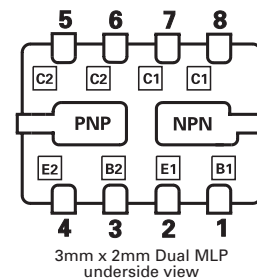
ORDERING INFORMATION

DEVICE	REEL	TAPE WIDTH	QUANTITY PER REEL
ZXTDB2M832TA	7''	8mm	3000
ZXTDB2M832TC	13''	8mm	10000

DEVICE MARKING

DB2

PINOUT



3mm x 2mm Dual MLP
underside view

OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	NPN	PNP	UNIT
Collector-Base Voltage	V_{CBO}	40	-25	V
Collector-Emitter Voltage	V_{CEO}	20	-20	V
Emitter-Base Voltage	V_{EBO}	7.5	-7.5	V
Peak Pulse Current	I_{CM}	12	-6	A
Continuous Collector Current (a)(f)	I_C	4.5	-3.5	A
Continuous Collector Current (b)(f)	I_C	5	-3.8	A
Base Current	I_B	1000		mA
Power Dissipation at TA=25°C (a)(f) Linear Derating Factor	P_D	1.5 12		W mW/°C
Power Dissipation at TA=25°C (b)(f) Linear Derating Factor	P_D	2.45 19.6		W mW/°C
Power Dissipation at TA=25°C (c)(f) Linear Derating Factor	P_D	1 8		W mW/°C
Power Dissipation at TA=25°C (d)(f) Linear Derating Factor	P_D	1.13 8		W mW/°C
Power Dissipation at TA=25°C (d)(g) Linear Derating Factor	P_D	1.7 13.6		W mW/°C
Power Dissipation at TA=25°C (e)(g) Linear Derating Factor	P_D	3 24		W mW/°C
Storage Temperature Range	T_{stg}	-55 to +150		°C
Junction Temperature	T_j	150		°C

THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)(f)	$R_{\theta JA}$	83.3	°C/W
Junction to Ambient (b)(f)	$R_{\theta JA}$	51	°C/W
Junction to Ambient (c)(f)	$R_{\theta JA}$	125	°C/W
Junction to Ambient (d)(f)	$R_{\theta JA}$	111	°C/W
Junction to Ambient (d)(g)	$R_{\theta JA}$	73.5	°C/W
Junction to Ambient (e)(g)	$R_{\theta JA}$	41.7	°C/W

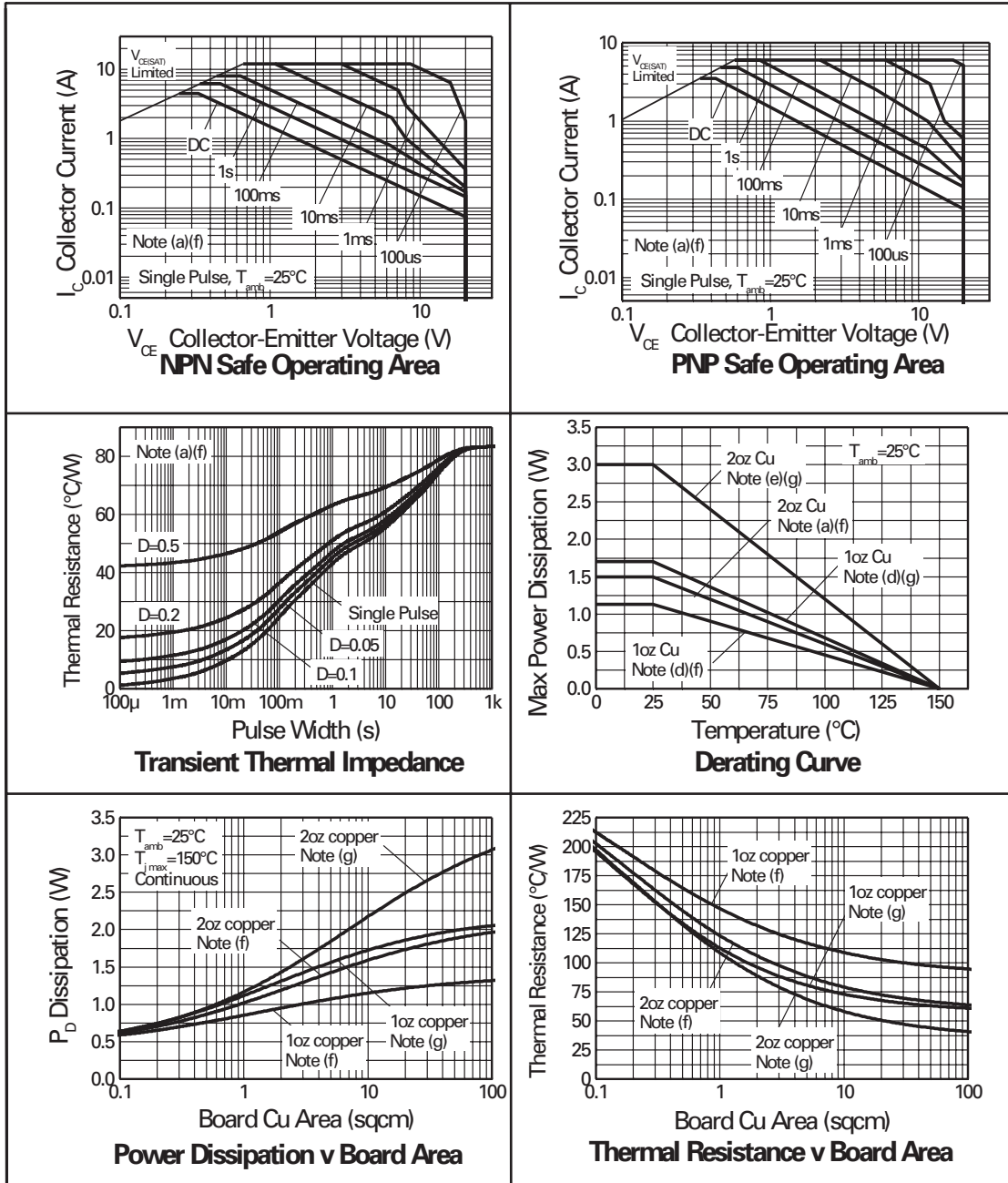
Notes

- (a) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (b) Measured at $t \leq 5$ secs for a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (c) For a dual device surface mounted on 8 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with minimal lead connections only**.
- (d) For a dual device surface mounted on 10 sq cm single sided 1oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (e) For a dual device surface mounted on 85 sq cm single sided 2oz copper on FR4 PCB, in still air conditions **with all exposed pads attached attached**. The copper area is split down the centre line into two separate areas with one half connected to each half of the dual device.
- (f) For a dual device with one active die.
- (g) For dual device with 2 active die running at equal power.
- (h) Repetitive rating - pulse width limited by max junction temperature. Refer to Transient Thermal Impedance graph.
- (i) The minimum copper dimensions required for mounting are no smaller than the exposed metal pads on the base of the device as shown in the package dimensions data. The thermal resistance for a dual device mounted on 1.5mm thick FR4 board using minimum copper 1 oz weight, 1mm wide tracks and one half of the device active is $R_{th} = 250^\circ\text{C/W}$ giving a power rating of $P_{tot} = 500\text{mW}$.

OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

TYPICAL CHARACTERISTICS



OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

NPN TRANSISTOR

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

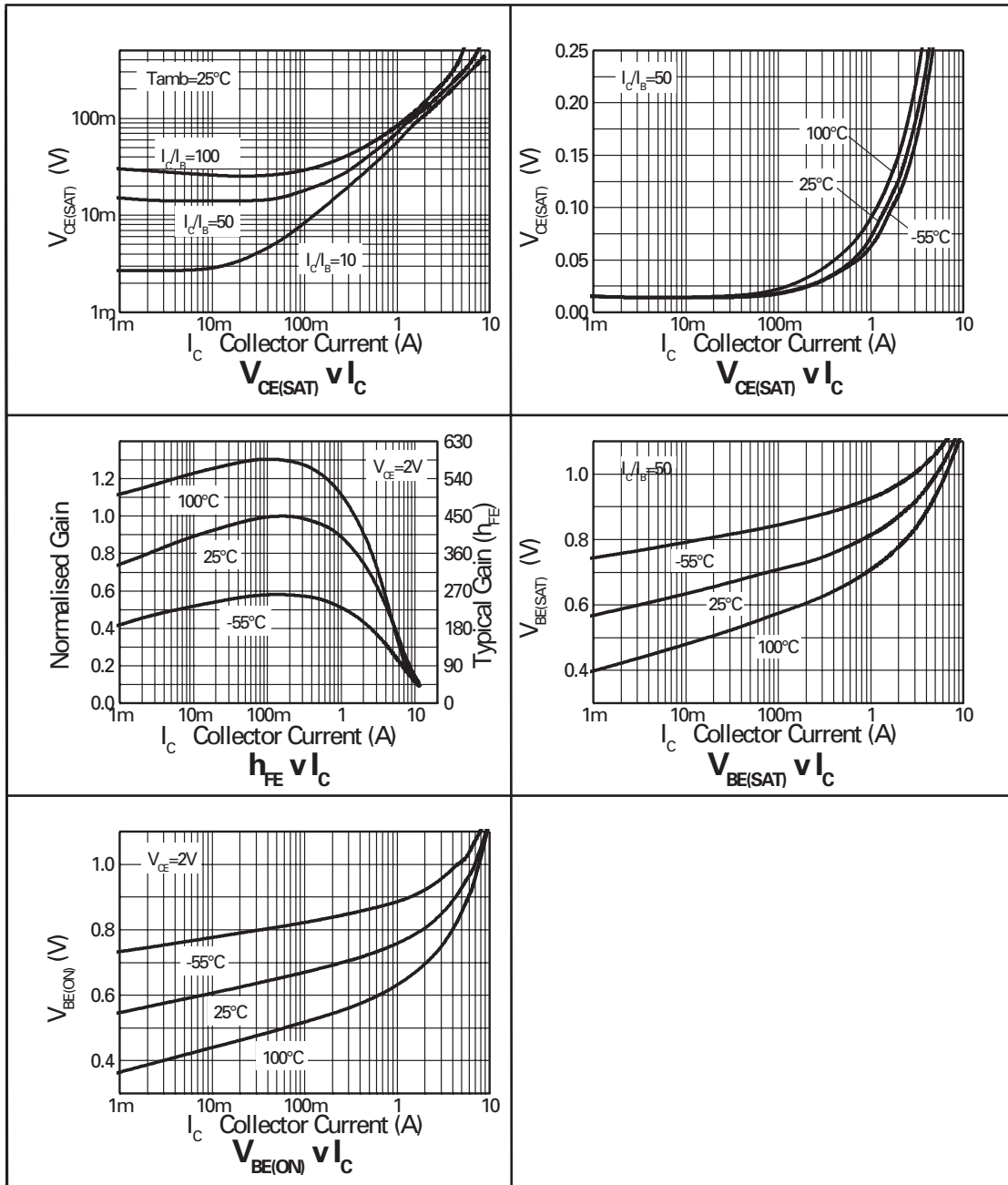
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	40	100		V	$I_C=100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	20	27		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7.5	8.2		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			25	nA	$V_{CB}=32\text{V}$
Emitter Cut-Off Current	I_{EBO}			25	nA	$V_{EB}=6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			25	nA	$V_{CE}=16\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		8 90 115 190 210	15 150 135 250 270	mV mV mV mV mV	$I_C=0.1\text{A}, I_B=10\text{mA}^*$ $I_C=1\text{A}, I_B=10\text{mA}^*$ $I_C=2\text{A}, I_B=50\text{mA}$ $I_C=3\text{A}, I_B=100\text{mA}$ $I_C=4.5\text{A}, I_B=125\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		0.98	1.05	V	$I_C=4.5\text{A}, I_B=125\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		0.88	0.95	V	$I_C=4.5\text{A}, V_{CE}=2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	200 300 200 100	400 450 360 180			$I_C=10\text{mA}, V_{CE}=2\text{V}^*$ $I_C=0.2\text{A}, V_{CE}=2\text{V}^*$ $I_C=2\text{A}, V_{CE}=2\text{V}^*$ $I_C=6\text{A}, V_{CE}=2\text{V}^*$
Transition Frequency	f_T	100	140		MHz	$I_C=50\text{mA}, V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		23	30	pF	$V_{CB}=10\text{V}, f=1\text{MHz}$
Turn-On Time	$t_{(on)}$		170		ns	$V_{CC}=10\text{V}, I_C=3\text{A}$
Turn-Off Time	$t_{(off)}$		400		ns	$I_{B1}=I_{B2}=10\text{mA}$

*Measured under pulsed conditions.

OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

NPN CHARACTERISTICS



OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

PNP TRANSISTOR

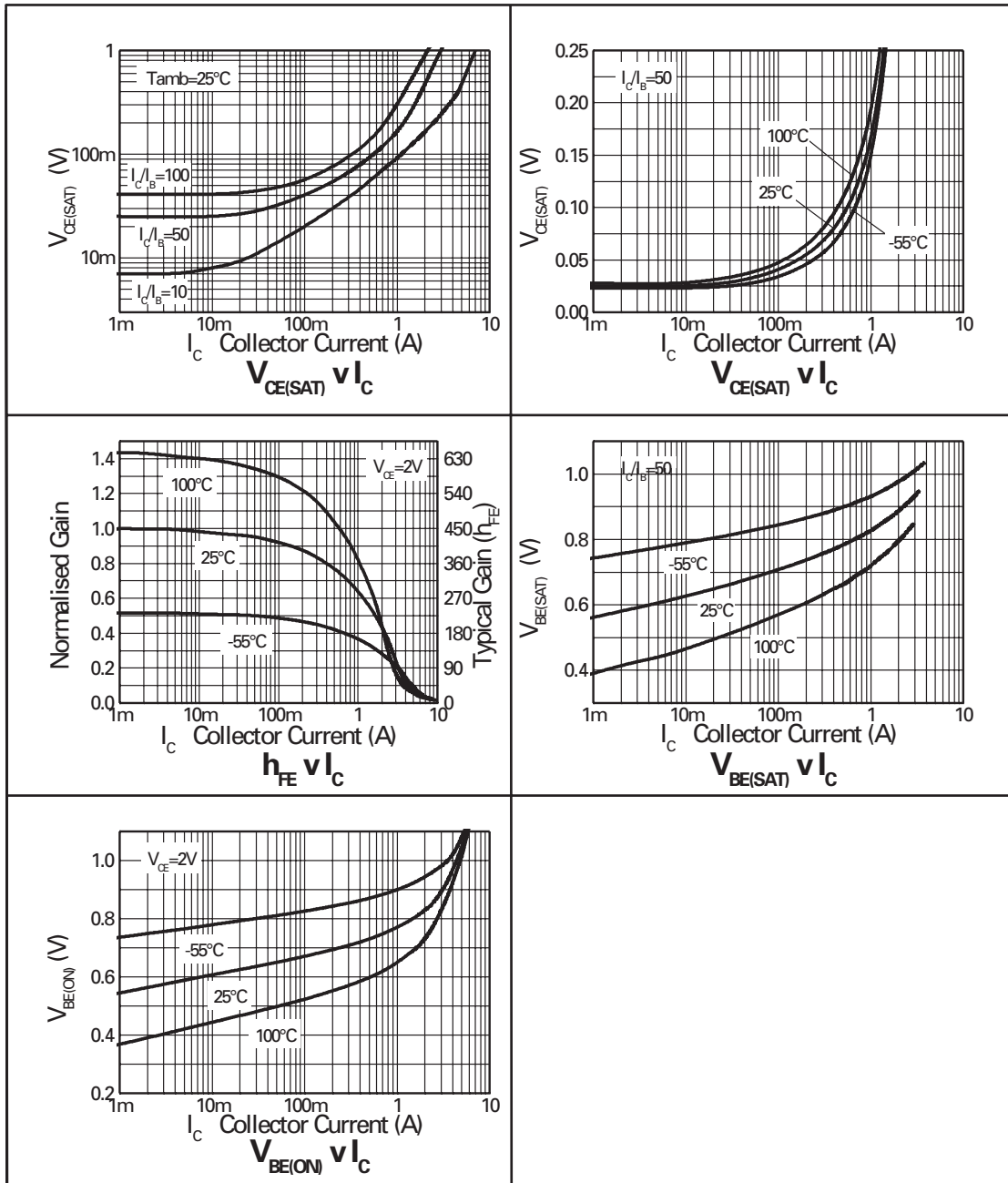
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-25	-35		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-20	-25		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-7.5	-8.5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-25	nA	$V_{CB} = -20\text{V}$
Emitter Cut-Off Current	I_{EBO}			-25	nA	$V_{EB} = -6\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-25	nA	$V_{CE} = -16\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-19 -170 -190 -240 -225	-30 -220 -250 -350 -300	mV mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -1\text{A}, I_B = -20\text{mA}^*$ $I_C = -1.5\text{A}, I_B = -50\text{mA}^*$ $I_C = -2.5\text{A}, I_B = -150\text{mA}^*$ $I_C = -3.5\text{A}, I_B = -350\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.10	-1.075	V	$I_C = -3.5\text{A}, I_B = -350\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.87	-0.95	V	$I_C = -3.5\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 150 15	475 450 230 30			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -6\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	150	180		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		21	30	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		40		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$
Turn-Off Time	$t_{(off)}$		670		ns	$I_{B1} = I_{B2} = 10\text{mA}$

*Measured under pulsed conditions.

ZXTDB2M832

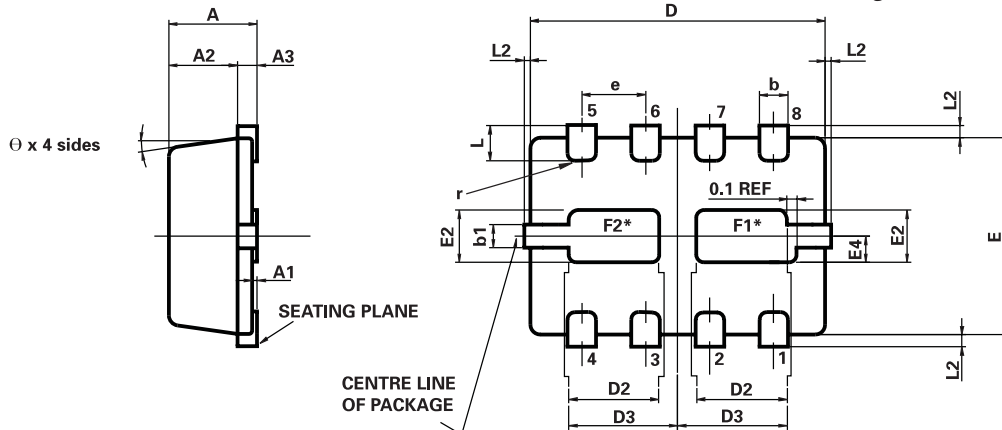
PNP CHARACTERISTICS



OBSOLETE - PLEASE USE ZXTC6718MC

ZXTDB2M832

MLP832 PACKAGE OUTLINE (3mm x 2mm Micro Leaded Package)



*Exposed Flags. Solder connection to improve thermal dissipation is optional.
 F1 at collector 1 potential
 F2 at collector 2 potential

CONTROLLING DIMENSIONS IN MILLIMETRES
 APPROX. CONVERTED DIMENSIONS IN INCHES

MLP832 PACKAGE DIMENSIONS

DIM	MILLIMETRES		INCHES		DIM	MILLIMETRES		INCHES	
	MIN.	MAX.	MIN.	MAX.		MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039	e	0.65 REF		0.0256	BSC
A1	0.00	0.05	0.00	0.002	E	2.00 BSC		0.0787	BSC
A2	0.65	0.75	0.0255	0.0295	E2	0.43	0.63	0.017	0.0249
A3	0.15	0.25	0.006	0.0098	E4	0.16	0.36	0.006	0.014
b	0.24	0.34	0.009	0.013	L	0.20	0.45	0.0078	0.0157
b1	0.17	0.30	0.0066	0.0118	L2		0.125	0.00	0.005
D	3.00 BSC		0.118 BSC		r	0.075 BSC		0.0029 BSC	
D2	0.82	1.02	0.032	0.040	θ	0°	12°	0°	12°
D3	1.01	1.21	0.0397	0.0476					

© Zetex plc 2002

Europe

Zetex plc
 Fields New Road
 Chadderton
 Oldham, OL9 8NP
 United Kingdom
 Telephone (44) 161 622 4422
 Fax: (44) 161 622 4420
 uksales@zetex.com

Zetex GmbH
 Streitfeldstraße 19
 D-81673 München
 Germany
 Telefon: (49) 89 45 49 49 0
 Fax: (49) 89 45 49 49 49
 europe.sales@zetex.com

Americas

Zetex Inc
 700 Veterans Memorial Hwy
 Hauppauge, NY11788
 USA
 Telephone: (631) 360 2222
 Fax: (631) 360 8222
 usa.sales@zetex.com

Asia Pacific

Zetex (Asia) Ltd
 3701-04 Metroplaza, Tower 1
 Hing Fong Road
 Kwai Fong
 Hong Kong
 Telephone: (852) 26100 611
 Fax: (852) 24250 494
 asia.sales@zetex.com

These offices are supported by agents and distributors in major countries world-wide.

This publication is issued to provide outline information only which (unless agreed by the Company in writing) may not be used, applied or reproduced for any purpose or form part of any order or contract or be regarded as a representation relating to the products or services concerned. The Company reserves the right to alter without notice the specification, design, price or conditions of supply of any product or service.

For the latest product information, log on to www.zetex.com



ISSUE 2 - JUNE 2002